# **DRC5114E**

### Silicon NPN epitaxial planar type

For digital circuits

Complementary to DRA5114E DRC2114E in SMini3 type package

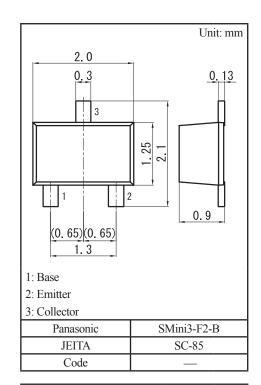
#### Features

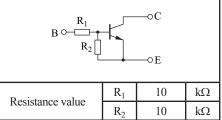
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)
- Marking Symbol: NB

#### Packaging

DRC5114E0L Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$								
Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V					
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V					
Collector current	I <sub>C</sub>	100	mA					
Total power dissipation	P <sub>T</sub>	150	mW					
Junction temperature	Tj	150	°C					
Storage temperature	T <sub>stg</sub>	-55 to +150	°C					



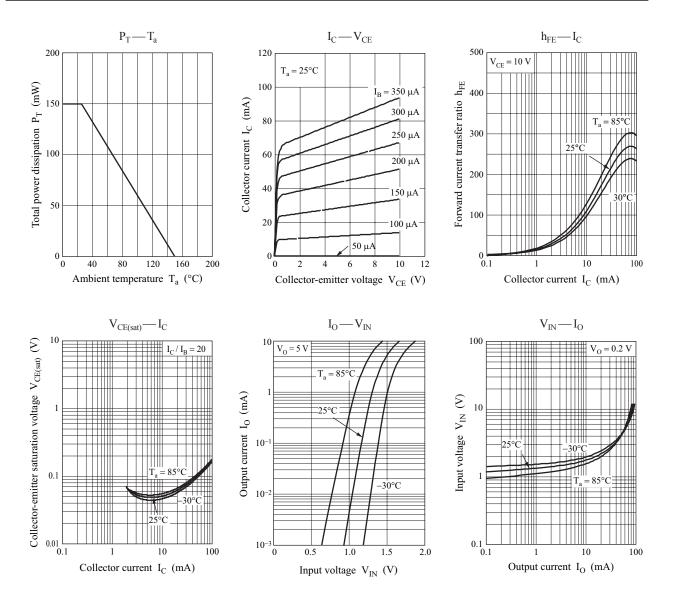


#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	50	Ì		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2  {\rm mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{\rm EB} = 6 \text{ V}, I_{\rm C} = 0$			0.5	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	35			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{CE} = 0.2 \text{ V}, I_C = 5 \text{ mA}$	2.1			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = 5 V, I_C = 100 \mu A$			0.8	V
Input resistance	R <sub>1</sub>		-30%	10	+30%	kΩ
Resistance ratio	R <sub>1</sub> / R <sub>2</sub>		0.8	1.0	1.2	

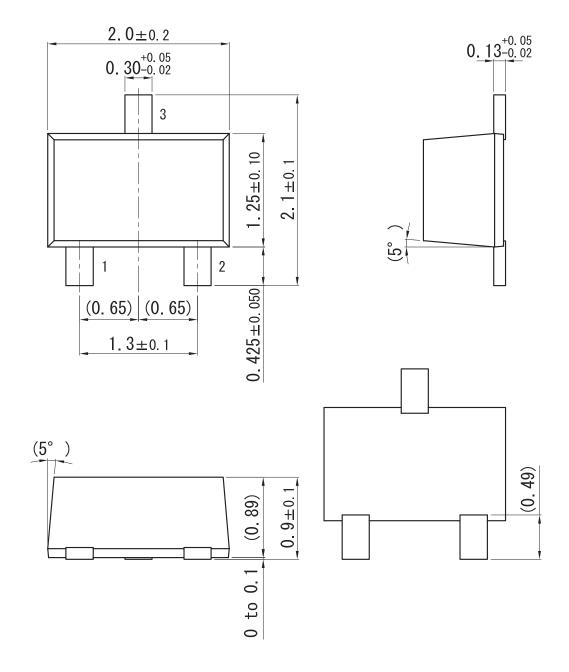
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## **Panasonic**

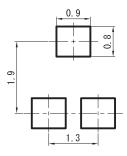


SMini3-F2-B





Land Pattern (Reference) (Unit: mm)



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